



#### 65V PNP SMALL SIGNAL TRANSISTOR IN DFN1110-3/SWP

#### **Features**

- BV<sub>CEO</sub> > -65V
- I<sub>C</sub> = -100mA High Continuous Collector Current
- Low-Profile, 0.6mm-High Package for Thin Applications
- Sidewall Tin Plating for Wettable Flanks in AOI
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- An automotive-compliant part is available under a separate datasheet (<u>BC856BFHWQ</u>).

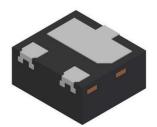
#### **Mechanical Data**

- Package: U-DFN1110-3/SWP
- Package Material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.001714 grams (Approximate)

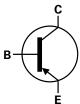
### **Application**

• Switching and amplification

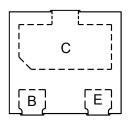
#### U-DFN1110-3/SWP (Type A)



**Bottom View** 



Device Symbol



Top View Pin-Out

### Ordering Information (Note 4)

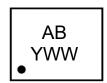
Orderable Bart Number	Orderable Part Number Package Marking		Reel Size	Tape Width	Packing	
Orderable Part Nulliber	Package	Warking	(inches)	(mm)	Qty.	Carrier
BC856BFHW-7	U-DFN1110-3/SWP (Type A)	4F	7	8	5,000	Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

## **Marking Information**

U-DFN1110-3/SWP (Type A)



AB = Product type Marking Code YWW = Date Code Marking Y = Last Digit of Year (ex: 5 = 2025) WW = Week Code 01 to 53



# Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	Vcво	-80	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-65	V
Emitter-Base Voltage	VEBO	-6	V
Continuous Collector Current	Ic	-100	mA
Peak Pulse Collector Current	I <sub>CM</sub>	-200	mA
Peak Base Current	Івм	-100	mA

# 

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 5)	PD	420	mW
Thermal Resistance, Junction to Ambient	(Note 5)	Reja	298	°C/W
Thermal Resistance, Junction to Case	(Note 6)	Rejc	109	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

## ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge – Charged Device Model	ESD CDM	1000	V	C3

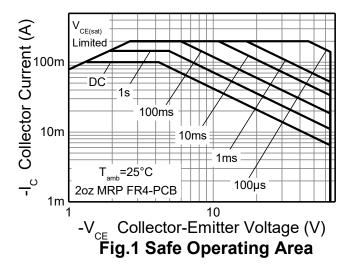
Notes:

<sup>5.</sup> For a device mounted with the exposed collector pads on minimum recommended pad layout that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

<sup>6.</sup> Thermal resistance from junction to the top of the case 7. Refer to JEDEC specification JESD22-A114 and JESD22-C101.



### **Thermal Characteristics and Derating Information**



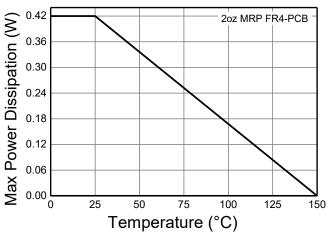
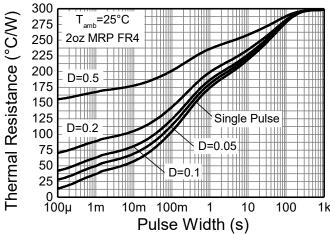


Fig.2 Derating Curve





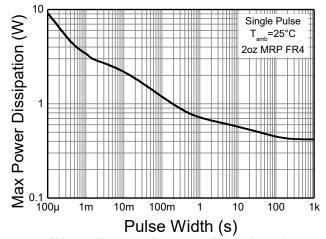


Fig.4 Pulse Power Dissipation



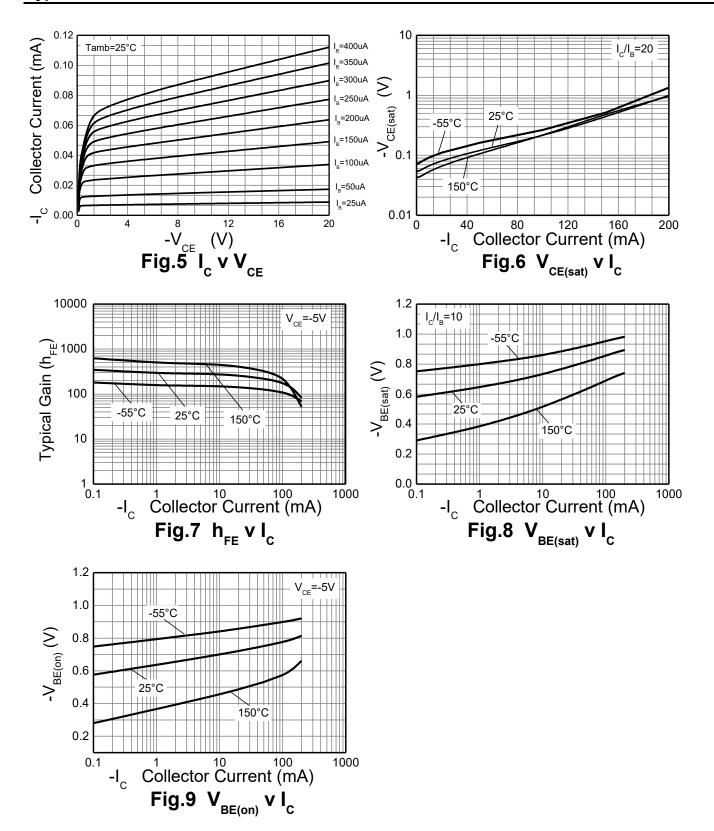
# **Electrical Characteristics** (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-80	_	_	V	I <sub>C</sub> = -100μA
Collector-Emitter Breakdown Voltage (Note 8)	BVceo	-65	_	_	V	Ic = -10mA
Emitter-Base Breakdown Voltage	BVEBO	-7	_	_	V	I <sub>E</sub> = -100μA
Collector-Base Cutoff Current	1		_	-15	nA	V <sub>CB</sub> = -30V, I <sub>E</sub> = 0
Collector-Base Cuton Current	ICBO		_	-5	μΑ	$V_{CB} = -30V$ , $I_E = 0$ , $T_A = +150$ °C
Emitter-Base Cutoff Current	I <sub>EBO</sub>	_	_	-100	nA	$V_{EB} = -5.6V, I_{C} = 0$
DC Current Gain	hfE	220	_	475	_	$V_{CE}$ = -5V, $I_C$ = -2mA
Oallantan Freitten Oatsmatien Walterna (Nata O)	VCE(sat)	_	_	-300	mV	$I_C = -10 \text{mA}, I_B = -0.5 \text{mA}$
Collector-Emitter Saturation Voltage (Note 8)			_	-650		I <sub>C</sub> = -100mA, I <sub>B</sub> = -5mA
Base Emitter Turn on Voltage (Note 9)	V	-600	_	-750	mV	V <sub>CE</sub> = -5V, I <sub>C</sub> = -2mA
Base-Emitter Turn-on Voltage (Note 8)	V <sub>BE(on)</sub>	_	_	-820		V <sub>CE</sub> = -5V, I <sub>C</sub> = -10mA
Base-Emitter Saturation Voltage (Note 8)	V <sub>BE(sat)</sub>		-700	_	V	I <sub>C</sub> = -10mA, I <sub>B</sub> = -0.5mA
Base-Emilier Saturation Voltage (Note 6)			-850	_	V	I <sub>C</sub> = -100mA, I <sub>B</sub> = -5mA
Transition Frequency	f⊤	100			MHz	V <sub>CE</sub> = -5V, I <sub>C</sub> = -10mA, f = 100MHz
Output (Collector) Capacitance	C <sub>obc</sub>	_	2	_	pF	V <sub>CB</sub> = -10V, f = 1MHz
Output (Emitter) Capacitance	Coec		10	_	pF	V <sub>EB</sub> = -0.5V, f = 1MHz
Noise Figure	NF	_	_	10	dB	$V_{CE}$ = -5V, I <sub>C</sub> = -200 $\mu$ A, R <sub>S</sub> = 2k $\Omega$ , f = 1kHz BW=200Hz

Note: 8. Measured under pulsed conditions. Pulse width  $\leq 300 \mu s$ . Duty cycle  $\leq 2\%$ .



## Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

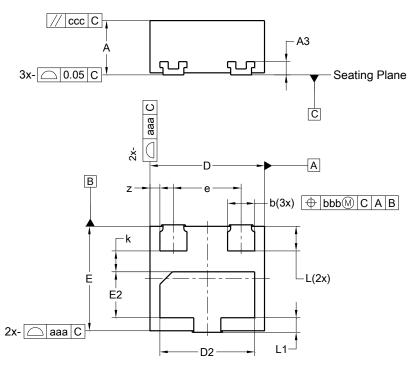




# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### U-DFN1110-3/SWP (Type A)



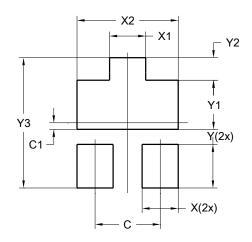
U-DFN1110-3/SWP						
	(Type A)					
Dim	Min	Max	Тур			
Α	0.47	0.57	0.52			
A1	0.00	0.05	0.03			
<b>A3</b>	_	_	0.127			
b	0.22	0.30	0.26			
D	1.05	1.15	1.10			
D2	0.87	0.95	0.91			
е	0.65 BSC					
Е	0.95	1.05	1.00			
E2	0.40	0.48	0.44			
k	-	_	0.20			
L	0.20	0.27	0.23			
L1	0.09	0.19	0.14			
Z	0.095					
aaa	0.25					
bbb	0.10					
CCC	0.10					
All Dimensions in mm						

Note: Side wall tin plated package for wettable flanks in AOI.

# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### U-DFN1110-3/SWP (Type A)



Dimensions	Value (in mm)		
C	0.650		
C1	0.065		
Х	0.360		
X1	0.360		
X2	1.010		
Υ	0.435		
Y1	0.490		
Y2	0.225		
Y3	1.300		



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